

Silicon NPN Power Transistors

2SD2539

DESCRIPTION

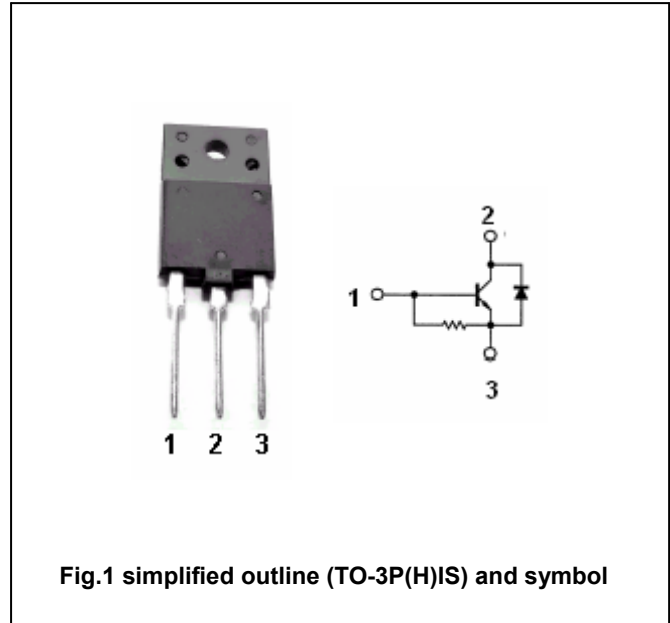
- With TO-3P(H)IS package
- High voltage ;high speed
- Low saturation voltage
- Bult-in damper diode

APPLICATIONS

- Horizontal deflection output for color TV

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings(Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
I_B	Base current		3.5	A
P_C	Total power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_C=400mA; I_B=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A; I_B=1.0A$			5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A; I_B=1.0A$		1.0	1.3	V
I_{CBO}	Collector cut-off current	$V_{CB}=1500V; I_E=0$			1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$	66		200	mA
h_{FE-1}	DC current gain	$I_C=1A; V_{CE}=5V$	8		28	
h_{FE-2}	DC current gain	$I_C=5A; V_{CE}=5V$	5		9	
V_F	Diode forward voltage	$I_F=5A$		1.6	2.0	V
C_{ob}	Collector output capacitance	$I_E=0; V_{CB}=10V, f=1MHz$		115		pF
f_T	Transition frequency	$I_C=0.1A; V_{CE}=10V$		2		MHz

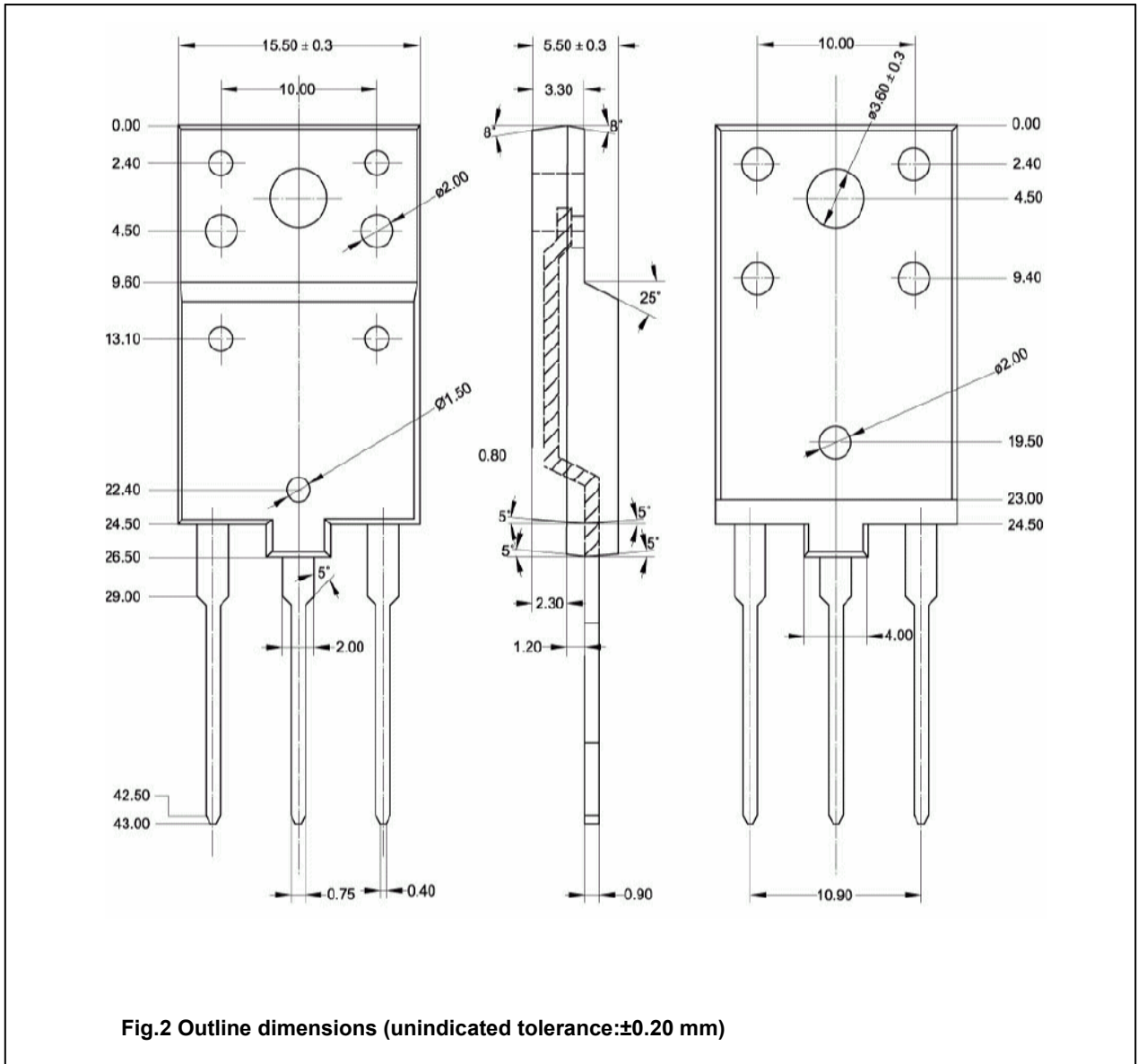
Switching times :

t_s	Storage time	$I_{CP}=5A; I_{B1}=1.0A$ $f_H=15.75kHz$		6	9	μs
t_f	Fall time			0.3	0.6	μs

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PACKAGE OUTLINE



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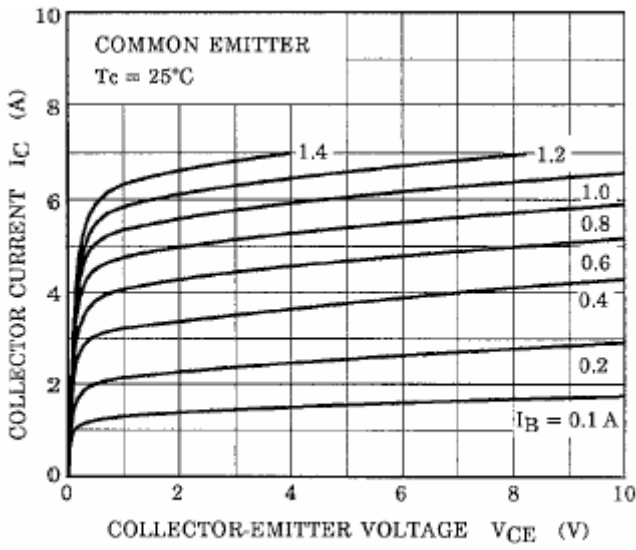


Fig.3 Static Characteristic

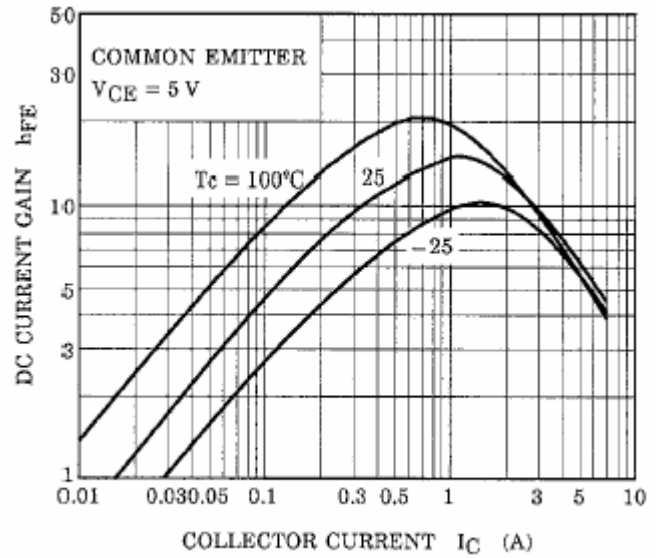


Fig.4 DC current Gain

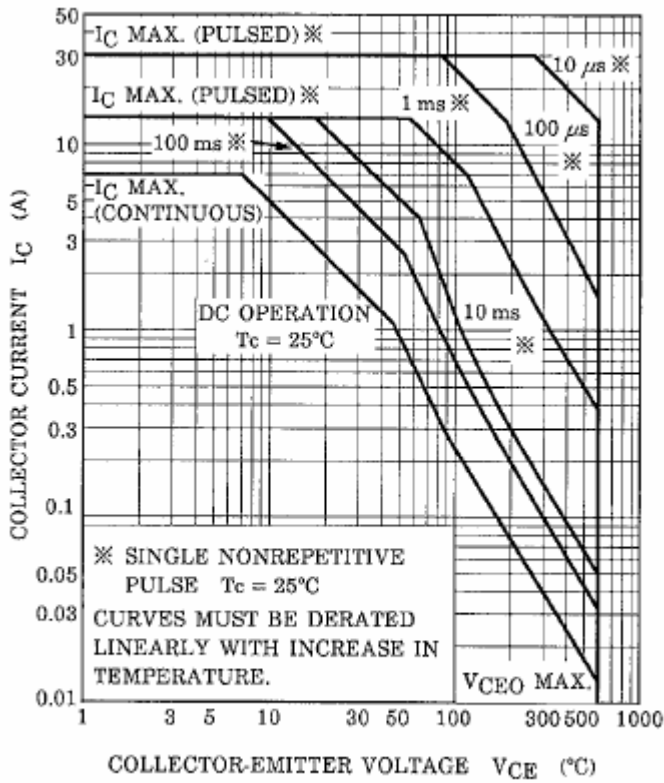


Fig.5 Safe Operating Area